

IN THE CLAIMS:

Please amend the claims as follows:

Claims 1-35 (Canceled).

36 (New). A method for manufacturing a semiconductor device that comprises a pixel matrix circuit and a driver circuit over a substrate comprising the steps of:

forming an active layer over a substrate;

forming a gate insulating film in contact with the active layer;

forming a gate wiring comprising tungsten as its main component over the gate insulating film using a resist mask; and

forming an impurity region by adding an impurity element using the gate wiring and the resist mask as a mask.

37 (New). The method according to claim 36,

wherein the gate wiring has a laminate structure comprising a tungsten film and a tungsten nitride film.

38 (New). The method according to claim 36,

wherein the gate wiring is formed using a sputtering method.

39 (New). A method for manufacturing a semiconductor device that comprises a pixel matrix circuit and a driver circuit over a substrate comprising the steps of:

forming an active layer over a substrate;

forming a gate insulating film in contact with the active layer;

forming a gate wiring comprising tungsten as its main component over the gate insulating film;

forming an impurity region by adding an impurity element using the gate wiring as a mask; and

forming a nitride film on a surface of the gate wiring by performing nitrification process onto the gate wiring.

40 (New). The method according to claim 39,
wherein the nitrification process is performed by generating plasma in an ammonium gas atmosphere.

41 (New). The method according to claim 39,
wherein the gate wiring has a laminate structure comprising a tungsten film and a tungsten nitride film.

42 (New). The method according to claim 39,
wherein the gate wiring is formed using a sputtering method.